LOW-POWER FIRST-IN, FIRST-OUT MEMORY

DL PACKAGE

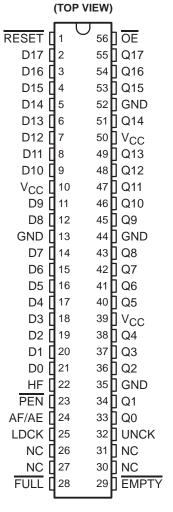
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- **Member of the Texas Instruments** Widebus™ Family
- Low-Power Advanced CMOS Technology
- Operates From 3-V to 3.6-V V_{CC}
- Load Clock and Unload Clock Can Be Asynchronous or Coincident
- Full, Empty, and Half-Full Flags
- **Programmable Almost-Full/Almost-Empty**
- Fast Access Times of 18 ns With a 50-pF Load and All Data Outputs Switching **Simultaneously**
- Data Rates up to 40 MHz
- 3-State Outputs
- Pin-to-Pin Compatible With SN74ACT7804, SN74ACT7806, and SN74ACT7814
- Packaged in Shrink Small-Outline 300-mil Package Using 25-mil Center-to-Center Spacing

description

A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. The SN74ALVC7806 is an 18-bit FIFO with high speed and fast access times. Data is processed at rates up to 40 MHz with access times of 18 ns in a bit-parallel format. These memories are designed for 3-V to 3.6-V V_{CC} operation.

Data is written into memory on a low-to-high transition of the load clock (LDCK) and is read out on a low-to-high transition of the unload clock



NC - No internal connection

(UNCK). The memory is full when the number of words clocked in exceeds the number of words clocked out by 256. When the memory is full, LDCK has no effect on the data residing in memory. When the memory is empty, UNCK has no effect.

Status of the FIFO memory is monitored by the full (FULL), empty (EMPTY), half-full (HF), and almostfull/almost-empty (AF/AE) flags. The FULL output is low when the memory is full and high when the memory is not full. The EMPTY output is low when the memory is empty and high when it is not empty. The HF output is high whenever the FIFO contains 128 or more words and low when it contains 127 or fewer words. The AF/AE status flag is a programmable flag. The first one or two low-to-high transitions of LDCK after reset are used to program the almost-empty offset value (X) and the almost-full offset value (Y) if program enable (\overline{PEN}) is low. The AF/AE flag is high when the FIFO contains X or fewer words or (256 – Y) or more words. The AF/AE flag is low when the FIFO contains between (X + 1) and (255 – Y) words.



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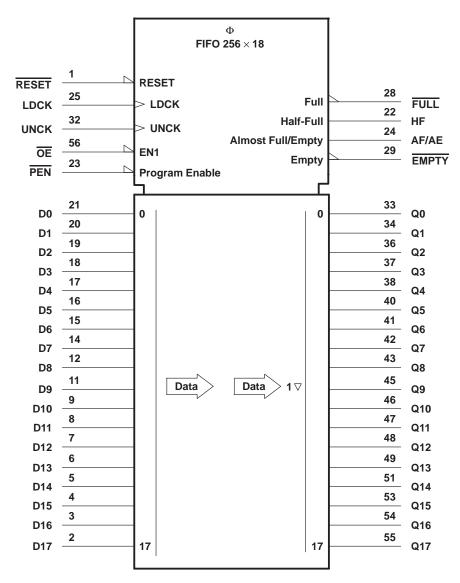
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description (continued)

A low level on the reset (RESET) resets the internal stack pointers and sets FULL high, AF/AE high, HF low, and EMPTY low. The Q outputs are not reset to any specific logic level. The FIFO must be reset on power up. The first word loaded into empty memory causes EMPTY to go high and the data to appear on the Q outputs. The data outputs are in the high-impedance state when the output-enable (OE) is high.

The SN74ALVC7806 is characterized for operation from 0°C to 70°C.

logic symbol†

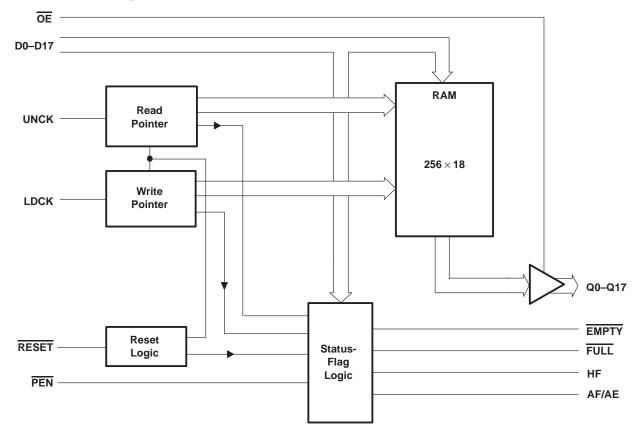


[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



CONCOUNT COTOBER 100

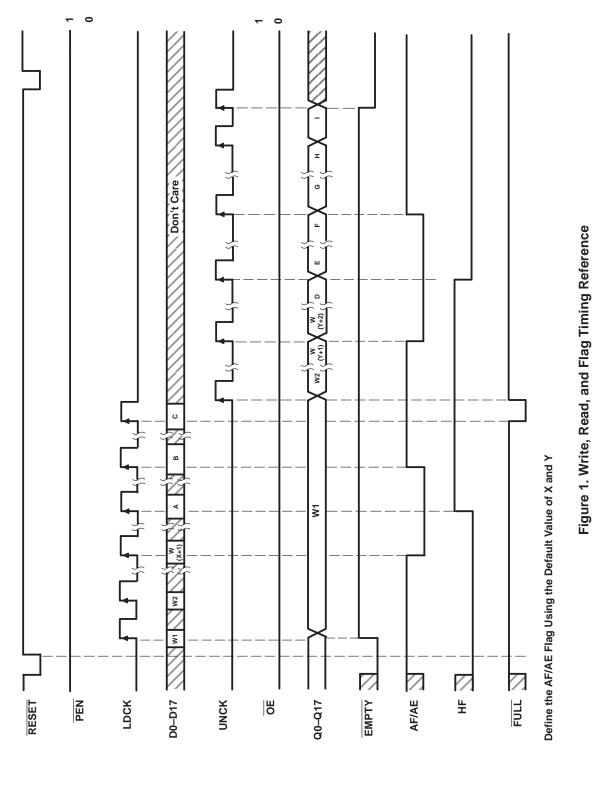
functional block diagram



Terminal Functions

TEI	TERMINAL		DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
AF/AE	24	0	Almost full/almost empty flag. Depth-offset values can be programmed for this flag or the default value of 64 can be used for both the almost empty offset (X) and the almost full offset (Y). AF/AE is high when memory contains X or fewer words or (256 – Y) or more words. AF/AE is high after reset.
D0-D17	2–9, 11–12, 14–21	-	18-bit data input port
EMPTY	29	0	Empty flag. EMPTY is low when the FIFO is empty. A FIFO reset also causes EMPTY to go low.
FULL	28	0	Full flag. FULL is low when the FIFO is full. A FIFO reset causes FULL to go high.
HF	22	0	Half-full flag. HF is high when the FIFO memory contains 128 or more words. HF is low after reset.
LDCK	25	I	Load clock. Data is written to the FIFO on the rising edge of LDCK when FULL is high.
OE	56	I	Output enable. When OE is high, the data outputs are in the high-impedance state.
PEN	23	-	Program enable. After reset and before the first word is written to the FIFO, the binary value on D0–D7 is latched as an AF/AE offset value when PEN is low and WRTCLK is high.
Q0-Q17	33–34, 36–38, 40–43, 45–49, 51, 53–55	0	18-bit data output port
RESET	1	I	Reset. A low level on RESET resets the FIFO and drives AF/AE and FULL high and HF and EMPTY low.
UNCK	32	I	Unload clock. Data is read from the FIFO on the rising edge of UNCK when EMPTY is high.





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DATA-WORD NUMBERS FOR FLAG TRANSITIONS

DEVICE				TR	ANSITIO	N WORD			
DEVICE	Α	В	С	D	E	F	G	Н	I
SN74ALVC7806	W128	W(256 – Y)	W256	W129	W130	W(256 – X)	W(257 – X)	W255	W256

Figure 1. Write, Read, and Flag Timing Reference (Continued)

offset values for AF/AE

The AF/AE flag has two programmable limits: the almost-empty offset value (X) and the almost-full offset value (Y). They can be programmed after the FIFO is reset and before the first word is written to memory. The AF/AE flag is high when the FIFO contains X or fewer words or (256 - Y) or more words.

To program the offset values, \overline{PEN} can be brought low after reset. On the following low-to-high transition of LDCK, the binary value on D0–D7 is stored as the almost-empty offset value (X) and the almost-full offset value (Y). Holding \overline{PEN} low for another low-to-high transition of LDCK reprograms Y to the binary value on D0–D7 at the time of the second LDCK low-to-high transition. Writes to the FIFO memory are disabled while the offsets are programmed. A maximum value of 127 can be programmed for either X or Y (see Figure 2). To use the default values of X = Y = 32, \overline{PEN} must be held high.

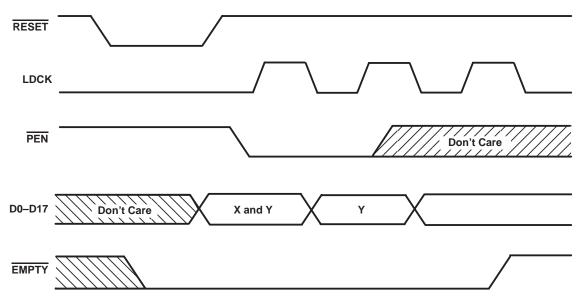


Figure 1. Programming X and Y Separately

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Output voltage range, V _O (see Notes 1 and 2)	
Voltage range applied to a disabled 3-state output	
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3)	74°C/W
Storage temperature range, T _{stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

					'ALVC78	UNIT			
			MIN	MAX	MIN	MAX	UNIT		
Vcc	V _{CC} Supply Voltage		3	3.6	3	3.6	V		
VIH	High-level input voltage		2		2	V			
VIL	/IL Low-level input voltage			0.8		0.8	V		
VI	V _I Input voltage				0	VCC	V		
٧o	Output voltage		0	Vcc	0	VCC	V		
IOH	High-level output current, Q outputs, flags	V _{CC} = 3 V		-8		-8	mA		
loL	Low-level output current, Q outputs, flags	V _{CC} = 3 V		16		16	mA		
TA	Operating free-air temperature		0	70	0	70	°C		

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	1	TEST CONDITIONS	MIN TY	YP‡ MAX	UNIT
V0	Flags, Q outputs	$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	I _{OH} = -100 μA	V _{CC} -0.2		V
VOH		$V_{CC} = 3 V$,	$I_{OH} = -8 \text{ mA}$	2.4		V
	Flags, Q outputs	$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	I _{OL} = 100 μA		0.2	
VOL	Flags	$V_{CC} = 3 V$,	$I_{OL} = 8 \text{ mA}$		0.4	V
	Q outputs	$V_{CC} = 3 V$,	$I_{OL} = 16 \text{ mA}$		0.55	
Ц		$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND		±5	μΑ
loz		$V_{CC} = 3.6 \text{ V},$	$V_O = V_{CC}$ or GND		±10	μΑ
Icc		V _{CC} = 3.6 V,	$V_I = V_{CC}$ or GND and $I_O = 0$		40	μΑ
∆lcc§		V _{CC} = 3.6 V, One input at	t V _{CC} -0.6 V, Other inputs at V _{CC} or GND		500	μΑ
Ci		V _{CC} = 3.3 V,	$V_I = V_{CC}$ or GND		3	pF
Co		V _{CC} = 3.3 V,	$V_O = V_{CC}$ or GND		6	pF

 $^{^{\}ddagger}$ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



[§] This is the supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

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timing requirements over recommended operating conditions (see Figures 1 through 3)

			'ALVC7806-25		'ALVC78	306-40	UNIT	
			MIN	MAX	MIN	MAX	UNII	
fclock	Clock frequency			40		25	MHz	
t _W		D0-D17 high or low	8		12			
		LDCK high or low	8		12		ns	
	Pulse duration	UNCK high or low	8		12			
		PEN low	8		12			
		RESET low	10		12			
		D0-D17 before LDCK↑	5		5			
t _{su}	Setup time	LDCK inactive before RESET high	6		6		ns	
t _{su} ;		PEN before LDCK↑	8		8			
		D0-D17 after LDCK↑	0		0			
۱	Hold time	PEN high after LDCK low	0		0		ns	
th	noid time	PEN low after LDCK↑	3		3			
		LDCK inactive after RESET high	6		6			

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 3)

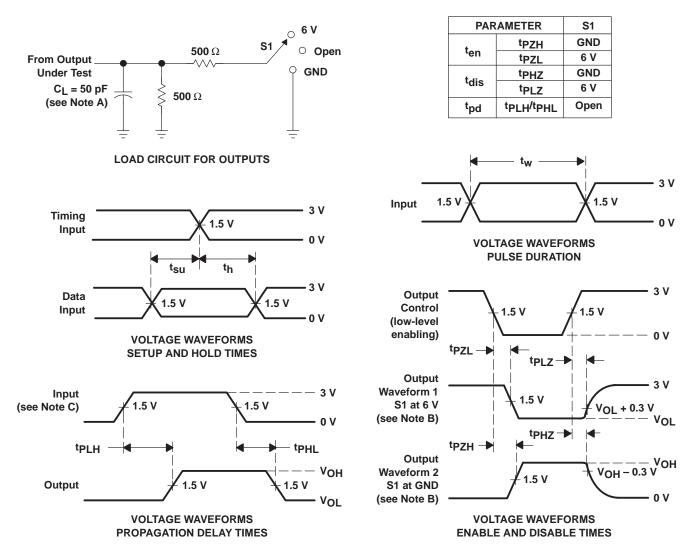
PARAMETER	FROM	то	'ALVC7	806-25	'ALVC78	306-40	UNIT
PARAMETER	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	UNII
f _{max}	LDCK or UNCK		40		25		MHz
.	LDCK [↑]	Any Q	9	22	9	24	
^t pd	UNCK↑	Ally Q	6	18	6	20	ns
^t PLH	LDCK↑	EMPTY	6	17	6	19	ns
	UNCK↑		6	17	6	19	9
^t PHL	RESET low	EMPTY	4	18	4	20	ns
	LDCK [↑]	FULL	6	17	6	19	
*	UNCK↑		6	17	6	19	
^t PLH	RESET low	FULL	4	20	4	22	ns
	LDCK↑	AF/AE	7	20	7	22	ns
^t pd	UNCK↑	AF/AE	7	20	7	22	115
t	RESET low	AF/AE	2	12	2	14	ns
^t PLH	LDCK [↑]	HF	5	20	5	22	115
t=	UNCK↑	HF	7	20	7	22	ns
^t PHL	RESET low		3	14	3	16	115
^t en	ŌE	Any Q	2	10	2	11	ns
t _{dis}	ŌE	Any Q	2	11	2	12	ns

operating characteristics, $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER			TEST CO	TYP	UNIT	
C _{pd}	Power dissipation capacitance per FIFO channel	Outputs enabled	$C_L = 50 \text{ pF},$	f = 5 MHz	53	pF



PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.

Figure 2. Standard CMOS Outputs (FULL, EMPTY, HF, AF/AE)



TYPICAL CHARACTERISTICS

SUPPLY CURRENT CLOCK FREQUENCY 140 f_{data} = 1/2 f_{clock} T_A = 75°C 120 $C_L = 0 pF$ I cc(f) - Supply Current - mA $V_{CC} = 3.6 V$ 100 $V_{CC} = 3.3 V$ 80 60 $V_{CC} = 3 V$ 40 20 10 30 40 50 60 70 80 90 f_{clock} - Clock Frequency - MHz

Figure 3

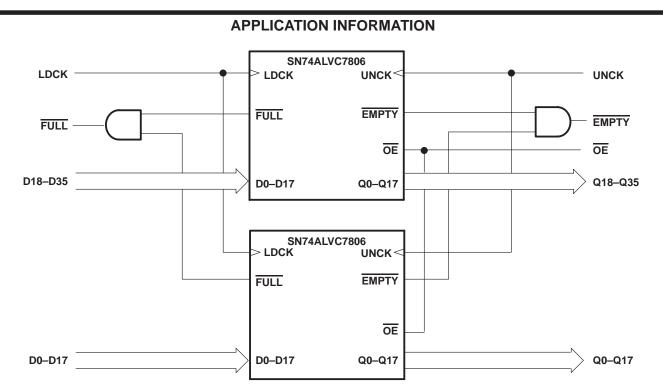


Figure 4. Word-Width Expansion: 256 imes 36 Bits



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